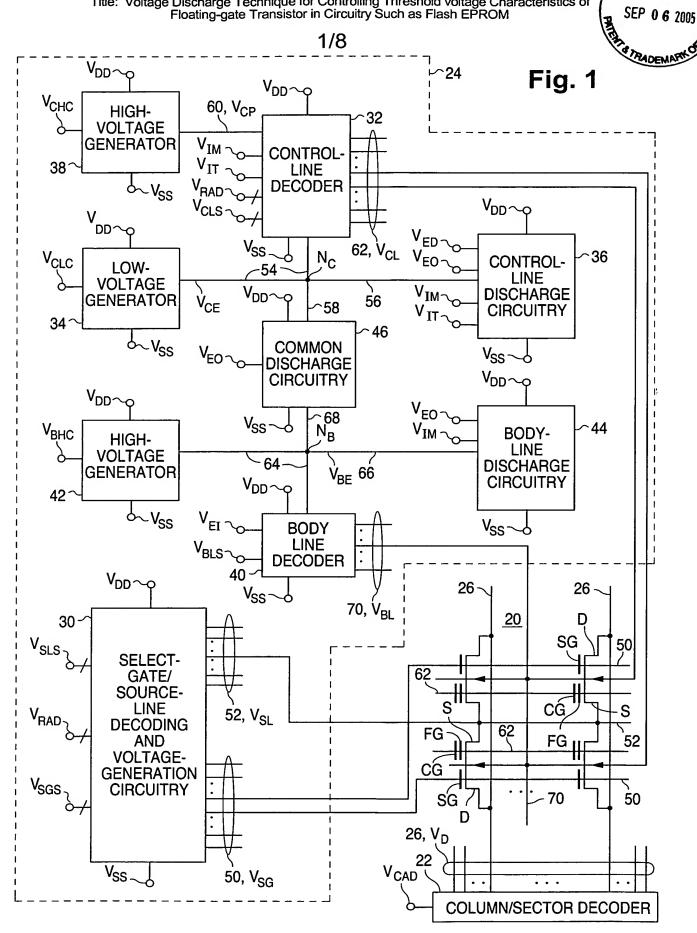
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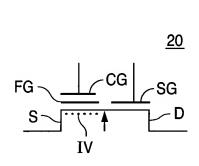


Fig. 2

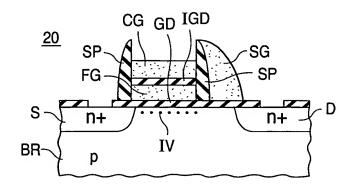


Fig. 3

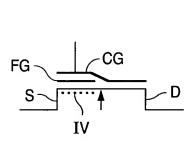


Fig. 6a

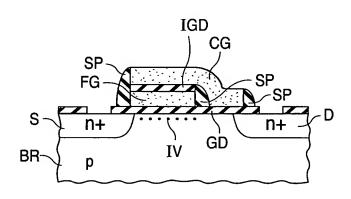


Fig. 7a

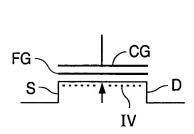


Fig. 7a

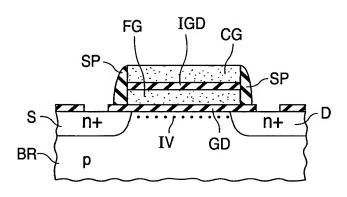
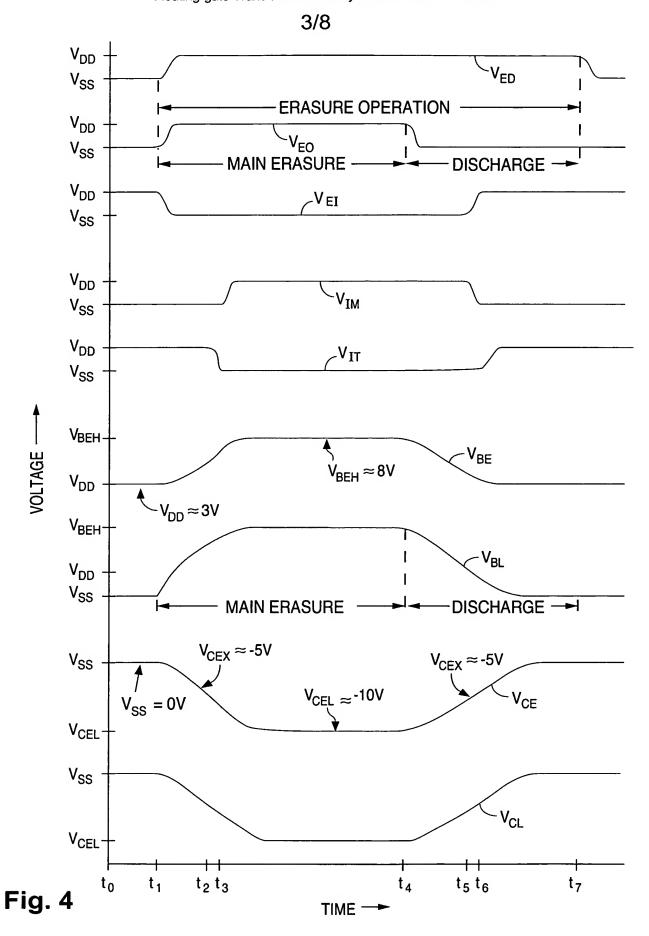


Fig. 7b



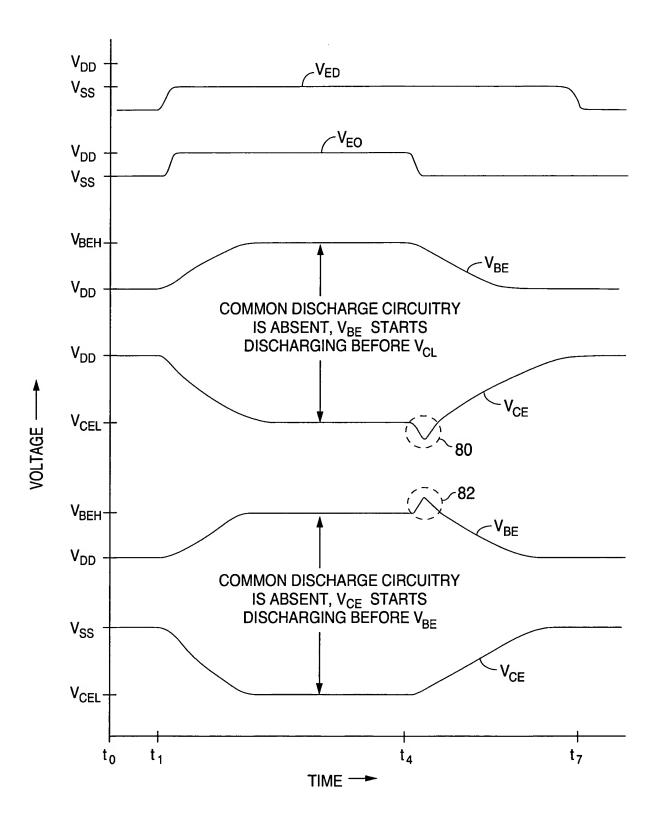
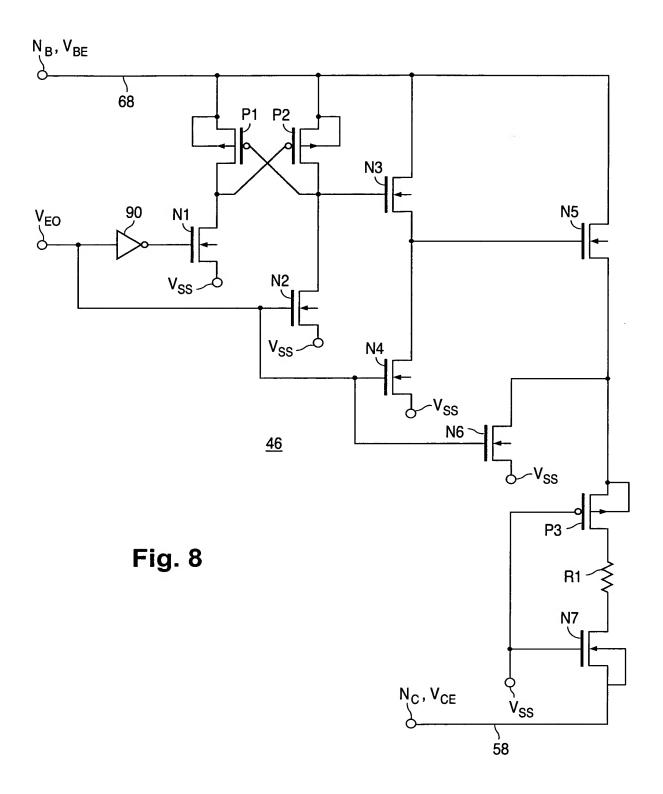


Fig. 5

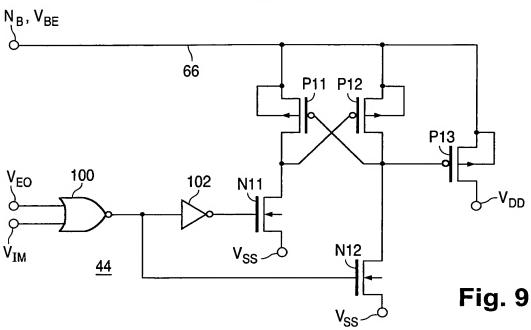


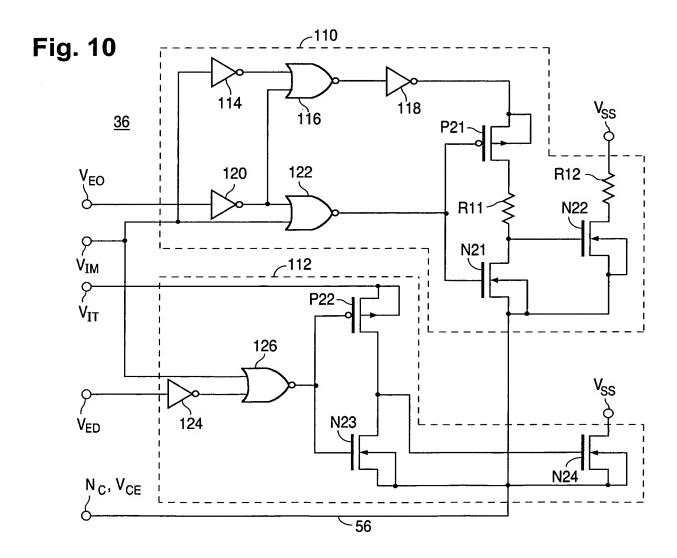
REPLACEMENT SHEET

NT SHEET

R-0004
Inventor: Park, Jongmin Appl'n No.: 10/780,030
Title: Voltage Discharge Technique for Controlling Threshold voltage Characteristics of Floating-gate Transistor in Circuitry Such as Flash EPROM







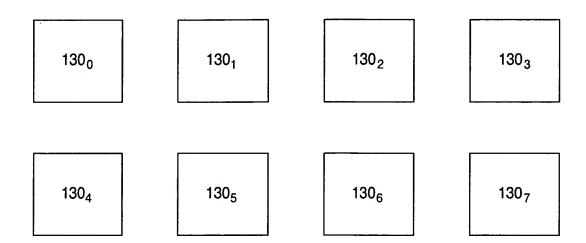
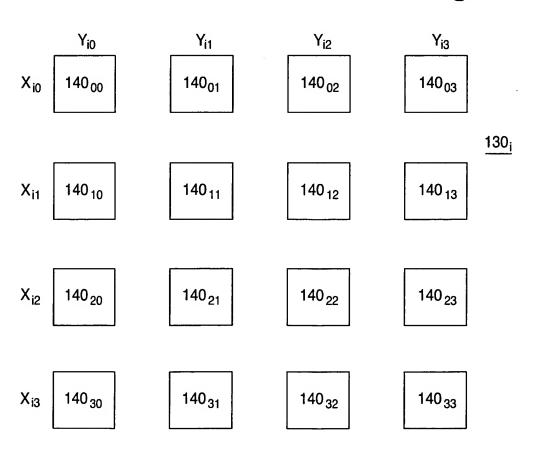


Fig. 11

Fig. 12



REPLACEMENT SHEET

Inventor: Park, Jongram Appl'n No.: 10/780,030

Title: Voltage Discharge Technique for Controlling Threshold voltage Characteristics of Floating-gate Transistor in Circuitry Such as Flash EPROM

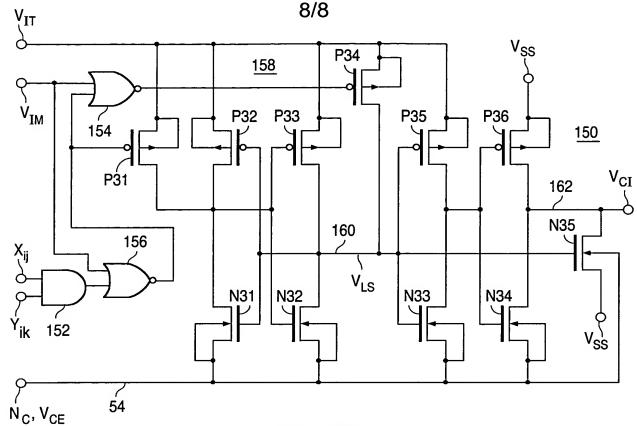


Fig. 13

